1.2 ± 0.05

0.8±0.05

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2131FV, RN2132FV

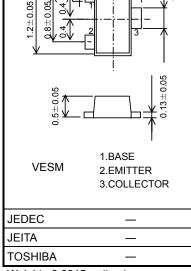
Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design •
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1131FV, RN1132FV

Equivalent Circuit

Maximum Ratings (Ta = 25°C)

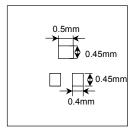
Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-100	mA
Collector power dissipation	P _C	150	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	-55~150	°C



 0.22 ± 0.05

c

Weight: 0.0015mg(typ.)



Note : Mounted on FR4 board (25.4 mm × 25.4 mm × 1.6 mmt)

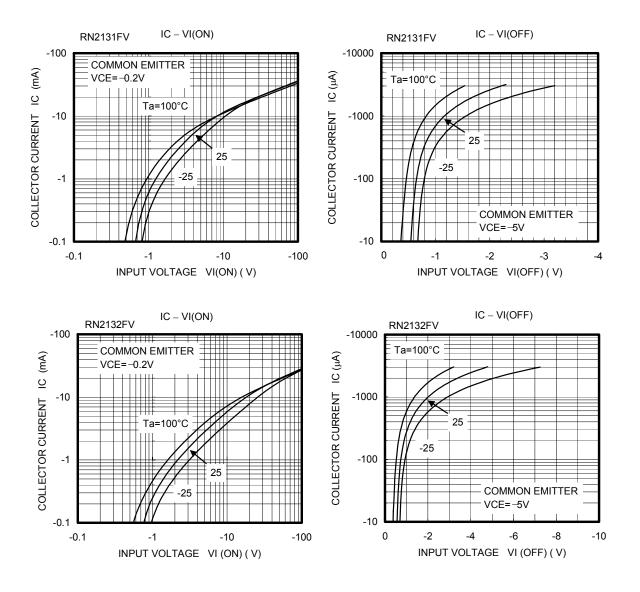
Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I _{CBO}	—	$V_{CB} = -50V, I_E = 0$	—	_	-100	nA
Emitter cut-off current		I _{EBO}	_	$V_{EB} = -5V, I_C = 0$	_	_	-100	nA
DC current gain		h _{FE}	—	V_{CE} = -5V, I _C = -1mA	120	_	400	
Collector-emitter saturation voltage		V _{CE (sat)}	—	I_{C} = -5mA, I_{B} = -0.25mA	—	-0.1	-0.3	V
Transition frequency		f _T	—	$V_{CE} = -10V, I_C = -5mA$	—	200	—	MHz
Collector output capacitance		C _{ob}	—	V_{CB} = -10V, I _E = 0, f = 1MH _z	_	3	—	pF
Input resistor	RN2131FV	R1 —			70	100	130	kΩ
	RN2132FV				140	200	260	

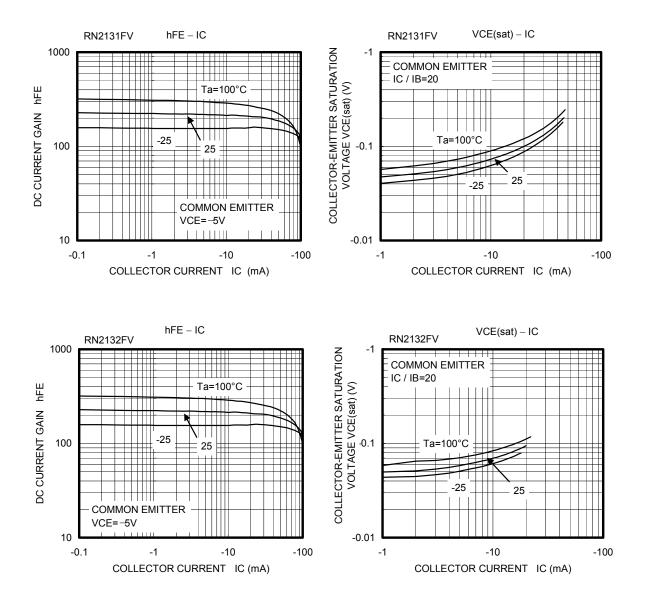
Unit : mm

0.32±0.05

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Type Name	Marking	
RN2131FV	Type Name Y 3	
RN2132FV	Type Name Y 4	

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